

## **isc** Silicon NPN RF Transistor

# **BFQ591**

#### **DESCRIPTION**

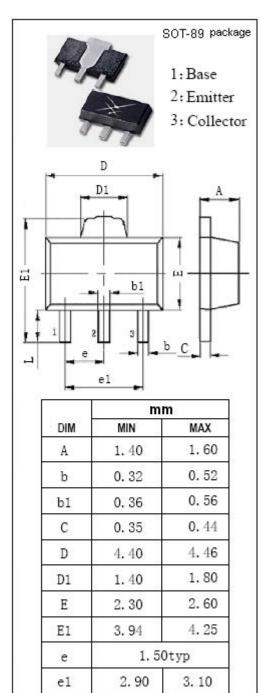
- · High Power Gain
- · High Current Gain Bandwidth Product
- · Low Noise Figure
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

 Designed for use in MATV or CATV amplifiers and RF communications subscribers equipment.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	20	٧
$V_{CEO}$	Collector-Emitter Voltage	15	V
V <sub>EBO</sub>	Emitter-Base Voltage	3	V
Ic	Collector Current-Continuous	200	mA
Pc	Collector Power Dissipation @Tc=25℃	2.25	W
TJ	Junction Temperature	175	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$ C



0.90

1.10

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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 0.1mA ; I <sub>B</sub> = 0	15			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 0.1m A ; I <sub>E</sub> = 0	20			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 0.1m A ; I <sub>C</sub> = 0	3			V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 10V; I <sub>E</sub> = 0			0.1	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 70mA ; V <sub>CE</sub> = 8V	60		250	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 70mA ; V <sub>CE</sub> = 12V; f= 1GHz		7		GHz
PG	Power Gain	I <sub>C</sub> = 70mA;V <sub>CE</sub> = 12V; f= 900MHz		11		dB
PG	Power Gain	I <sub>C</sub> = 70mA;V <sub>CE</sub> = 12V; f= 2GHz		5.5		dB
Cre	Feedback Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 12V; f= 1MHz		0.8		pF
S <sub>21e</sub>   <sup>2</sup>	Insertion Power Gain	I <sub>C</sub> = 70mA ; V <sub>CE</sub> = 12V; f= 1GHz		10		dB
Vo	Output Voltage	note		700		mV

Note:  $d_{im}$  = 60 dB (DIN45004B);  $V_p$  =  $V_o$ ;  $V_q$  =  $V_o$  -6 dB;  $f_p$  = 795.25 MHz;  $f_q$  = 803.25 MHz;  $f_r$  = 803.25 MHz; measured @  $f_{(p+q+r)}$  = 793.25 MHz.

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